

# MOSFET - Power, Single N-Channel

## 100 V, 1.7 mΩ, 267 A

### NTMTSC1D6N10MC

#### Features

- Small Footprint (8x8 mm) for Compact Design
- Low  $R_{DS(on)}$  to Minimize Conduction Losses
- Low  $Q_G$  and Capacitance to Minimize Driver Losses
- New Power 88 Dual Cool Package
- These Devices are Pb-Free and are RoHS Compliant

#### MAXIMUM RATINGS ( $T_J = 25^\circ\text{C}$ unless otherwise noted)

| Parameter                                                                      | Symbol         | Value                                          | Unit             |
|--------------------------------------------------------------------------------|----------------|------------------------------------------------|------------------|
| Drain-to-Source Voltage                                                        | $V_{DS}$       | 100                                            | V                |
| Gate-to-Source Voltage                                                         | $V_{GS}$       | $\pm 20$                                       | V                |
| Continuous Drain Current $R_{\theta JC}$ (Notes 1, 3)                          | $I_D$          | $T_C = 25^\circ\text{C}$                       | A                |
|                                                                                |                | $T_C = 100^\circ\text{C}$                      |                  |
| Power Dissipation $R_{\theta JC}$ (Note 1)                                     | $P_D$          | $T_C = 25^\circ\text{C}$                       | W                |
|                                                                                |                | $T_C = 100^\circ\text{C}$                      |                  |
| Continuous Drain Current $R_{\theta JA}$ (Notes 1, 2, 3)                       | $I_D$          | $T_A = 25^\circ\text{C}$                       | A                |
|                                                                                |                | $T_A = 100^\circ\text{C}$                      |                  |
| Power Dissipation $R_{\theta JA}$ (Notes 1, 2)                                 | $P_D$          | $T_A = 25^\circ\text{C}$                       | W                |
|                                                                                |                | $T_A = 100^\circ\text{C}$                      |                  |
| Pulsed Drain Current                                                           | $I_{DM}$       | $T_A = 25^\circ\text{C}, t_p = 10 \mu\text{s}$ | A                |
| Operating Junction and Storage Temperature Range                               | $T_J, T_{stg}$ | $-55$ to $+175$                                | $^\circ\text{C}$ |
| Source Current (Body Diode)                                                    | $I_S$          | 243                                            | A                |
| Single Pulse Drain-to-Source Avalanche Energy ( $I_{L(pk)} = 22.3 \text{ A}$ ) | $E_{AS}$       | 1550                                           | mJ               |
| Lead Temperature for Soldering Purposes (1/8" from case for 10 s)              | $T_L$          | 260                                            | $^\circ\text{C}$ |

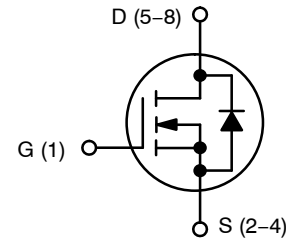
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

#### THERMAL RESISTANCE MAXIMUM RATINGS

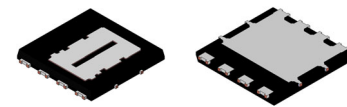
| Parameter                                   | Symbol           | Value | Unit               |
|---------------------------------------------|------------------|-------|--------------------|
| Junction-to-Case - Bottom - Steady State    | $R_{\theta JCB}$ | 0.5   | $^\circ\text{C/W}$ |
| Junction-to-Case - Top - Steady State       | $R_{\theta JCT}$ | 0.8   |                    |
| Junction-to-Ambient - Steady State (Note 2) | $R_{\theta JA}$  | 38    |                    |

1. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.
2. Surface-mounted on FR4 board using a 650 mm<sup>2</sup>, 2 oz. Cu pad.
3. Maximum current for pulses as long as 1 second is higher but is dependent on pulse duration and duty cycle.

| $V_{(BR)DSS}$ | $R_{DS(ON)} \text{ MAX}$ | $I_D \text{ MAX}$ |
|---------------|--------------------------|-------------------|
| 100 V         | 1.7 mΩ @ 10 V            | 267 A             |

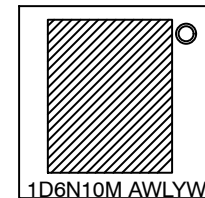


N-CHANNEL MOSFET



TDFNW8  
CASE 507AS

#### MARKING DIAGRAM



1D6N10M = Specific Device Code  
A = Assembly Location  
WL = Wafer Lot Code  
Y = Year Code  
W = Work Week Code

#### ORDERING INFORMATION

See detailed ordering, marking and shipping information in the package dimensions section on page 5 of this data sheet.

# NTMTSC1D6N10MC

## ELECTRICAL CHARACTERISTICS ( $T_J = 25^\circ\text{C}$ unless otherwise specified)

| Parameter | Symbol | Test Condition | Min | Typ | Max | Unit |
|-----------|--------|----------------|-----|-----|-----|------|
|-----------|--------|----------------|-----|-----|-----|------|

### OFF CHARACTERISTICS

|                                                           |                   |                                                     |                                  |      |     |                      |
|-----------------------------------------------------------|-------------------|-----------------------------------------------------|----------------------------------|------|-----|----------------------|
| Drain-to-Source Breakdown Voltage                         | $V_{(BR)DSS}$     | $V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$ | 100                              |      |     | V                    |
| Drain-to-Source Breakdown Voltage Temperature Coefficient | $V_{(BR)DSS}/T_J$ |                                                     |                                  | 64.5 |     | mV/ $^\circ\text{C}$ |
| Zero Gate Voltage Drain Current                           | $I_{DSS}$         | $V_{GS} = 0\text{ V}, V_{DS} = 100\text{ V}$        | $T_J = 25\text{ }^\circ\text{C}$ |      | 5   | $\mu\text{A}$        |
|                                                           |                   |                                                     | $T_J = 125^\circ\text{C}$        |      | 10  |                      |
| Gate-to-Source Leakage Current                            | $I_{GSS}$         | $V_{DS} = 0\text{ V}, V_{GS} = 20\text{ V}$         |                                  |      | 100 | nA                   |

### ON CHARACTERISTICS (Note 4)

|                                   |                  |                                                 |     |      |     |                      |
|-----------------------------------|------------------|-------------------------------------------------|-----|------|-----|----------------------|
| Gate Threshold Voltage            | $V_{GS(TH)}$     | $V_{GS} = V_{DS}, I_D = 650\text{ }\mu\text{A}$ | 2.0 |      | 4.0 | V                    |
| Threshold Temperature Coefficient | $V_{GS(TH)}/T_J$ |                                                 |     | -10  |     | mV/ $^\circ\text{C}$ |
| Drain-to-Source On Resistance     | $R_{DS(on)}$     | $V_{GS} = 10\text{ V}, I_D = 90\text{ A}$       |     | 1.42 | 1.7 | $\text{m}\Omega$     |
|                                   |                  | $V_{GS} = 6\text{ V}, I_D = 58\text{ A}$        |     |      | 4.3 |                      |
| Forward Transconductance          | $g_{FS}$         | $V_{DS} = 5\text{ V}, I_D = 100\text{ A}$       |     | 233  |     | S                    |

### CHARGES, CAPACITANCES & GATE RESISTANCE

|                              |              |                                                                  |  |      |  |             |
|------------------------------|--------------|------------------------------------------------------------------|--|------|--|-------------|
| Input Capacitance            | $C_{ISS}$    | $V_{GS} = 0\text{ V}, f = 100\text{ KHz}, V_{DS} = 50\text{ V}$  |  | 7630 |  | $\text{pF}$ |
| Output Capacitance           | $C_{OSS}$    |                                                                  |  | 4260 |  |             |
| Reverse Transfer Capacitance | $C_{RSS}$    |                                                                  |  | 80   |  |             |
| Total Gate Charge            | $Q_{G(TOT)}$ | $V_{GS} = 10\text{ V}, V_{DS} = 50\text{ V}; I_D = 116\text{ A}$ |  | 106  |  | $\text{nC}$ |
| Threshold Gate Charge        | $Q_{G(TH)}$  | $V_{GS} = 10\text{ V}, V_{DS} = 50\text{ V}; I_D = 116\text{ A}$ |  | 20   |  |             |
| Gate-to-Source Charge        | $Q_{GS}$     |                                                                  |  | 35   |  |             |
| Gate-to-Drain Charge         | $Q_{GD}$     |                                                                  |  | 22   |  |             |
| Plateau Voltage              | $V_{GP}$     |                                                                  |  | 5    |  | V           |

### SWITCHING CHARACTERISTICS (Note 5)

|                     |              |                                                                                         |  |    |  |    |
|---------------------|--------------|-----------------------------------------------------------------------------------------|--|----|--|----|
| Turn-On Delay Time  | $t_{d(ON)}$  | $V_{GS} = 10\text{ V}, V_{DS} = 50\text{ V}, I_D = 116\text{ A}, R_G = 6\text{ }\Omega$ |  | 34 |  | ns |
| Rise Time           | $t_r$        |                                                                                         |  | 24 |  |    |
| Turn-Off Delay Time | $t_{d(OFF)}$ |                                                                                         |  | 69 |  |    |
| Fall Time           | $t_f$        |                                                                                         |  | 29 |  |    |

### DRAIN-SOURCE DIODE CHARACTERISTICS

|                         |                 |                                                                                  |                        |  |      |     |    |
|-------------------------|-----------------|----------------------------------------------------------------------------------|------------------------|--|------|-----|----|
| Forward Diode Voltage   | V <sub>SD</sub> | V <sub>GS</sub> = 0 V,<br>I <sub>S</sub> = 90 A                                  | T <sub>J</sub> = 25°C  |  | 0.83 | 1.2 | V  |
|                         |                 |                                                                                  | T <sub>J</sub> = 125°C |  | 0.7  |     |    |
| Reverse Recovery Time   | t <sub>RR</sub> | V <sub>GS</sub> = 0 V, dI <sub>S</sub> /dt = 100 A/μs,<br>I <sub>S</sub> = 58 A  |                        |  | 54   |     | ns |
| Charge Time             | t <sub>a</sub>  |                                                                                  |                        |  | 26   |     |    |
| Discharge Time          | t <sub>b</sub>  |                                                                                  |                        |  | 28   |     |    |
| Reverse Recovery Charge | Q <sub>RR</sub> |                                                                                  |                        |  | 52   |     | nC |
| Reverse Recovery Time   | t <sub>RR</sub> | V <sub>GS</sub> = 0 V, dI <sub>S</sub> /dt = 1000 A/μs,<br>I <sub>S</sub> = 58 A |                        |  | 43   |     | ns |
| Charge Time             | t <sub>a</sub>  |                                                                                  |                        |  | 23   |     |    |
| Discharge Time          | t <sub>b</sub>  |                                                                                  |                        |  | 19   |     |    |
| Reverse Recovery Charge | Q <sub>RR</sub> |                                                                                  |                        |  | 385  |     | nC |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. Pulse Test: pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .

5. Switching characteristics are independent of operating junction temperatures.

TYPICAL CHARACTERISTICS

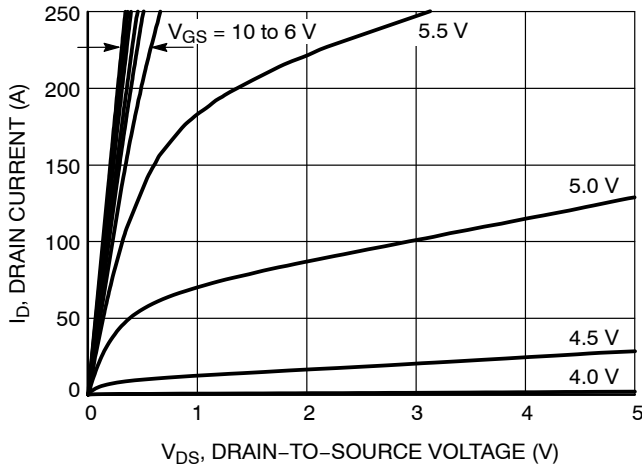


Figure 1. On-Region Characteristics

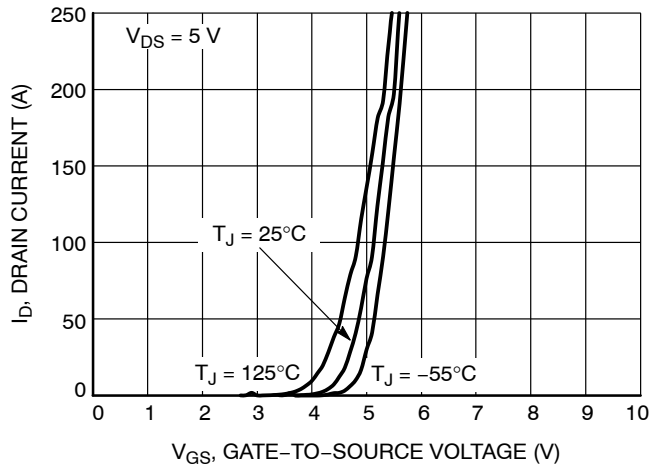


Figure 2. Transfer Characteristics

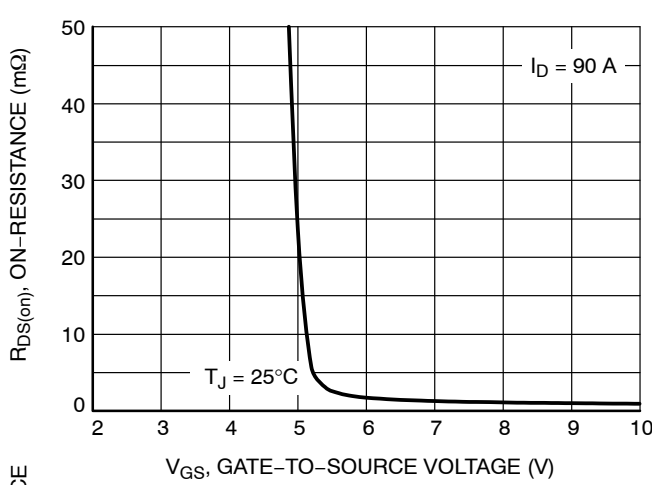


Figure 3. On-Resistance vs. Gate-to-Source Voltage

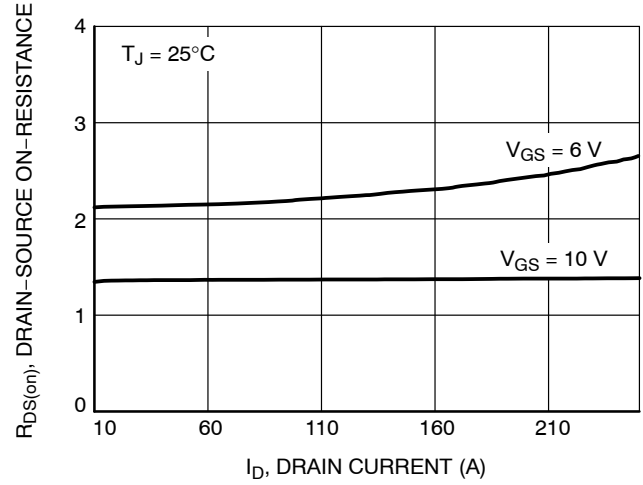


Figure 4. On-Resistance vs. Drain Current

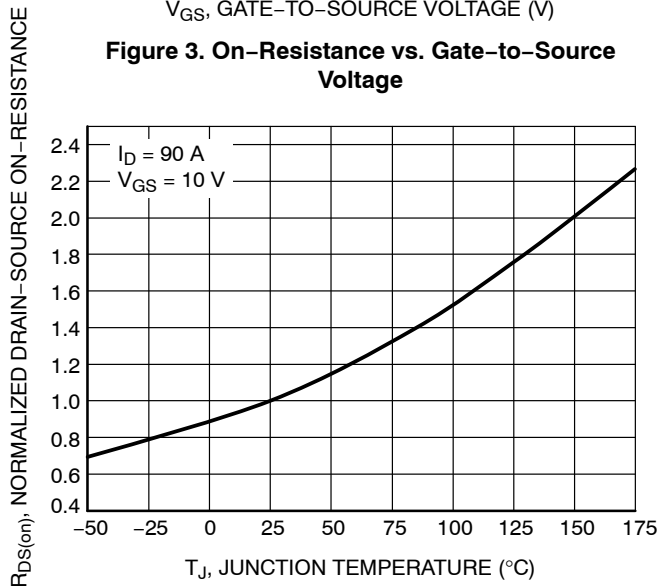


Figure 5. On-Resistance Variation with Temperature

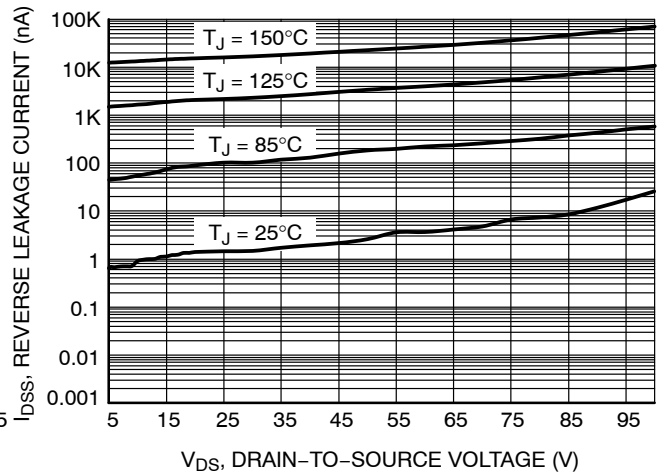


Figure 6. Drain-to-Source Leakage Current vs. Voltage

# NTMTSC1D6N10MC

## TYPICAL CHARACTERISTICS

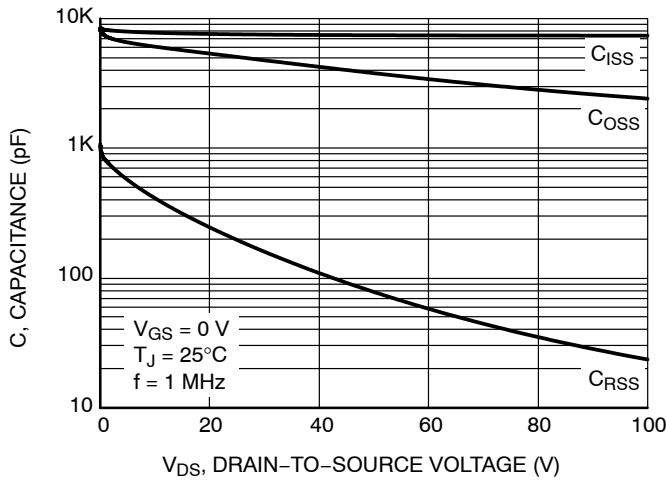


Figure 7. Capacitance Variation

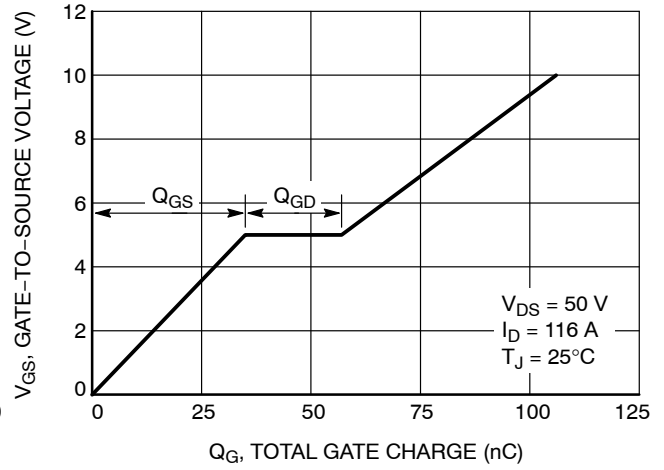


Figure 8. Gate-to-Source Voltage vs. Total Charge

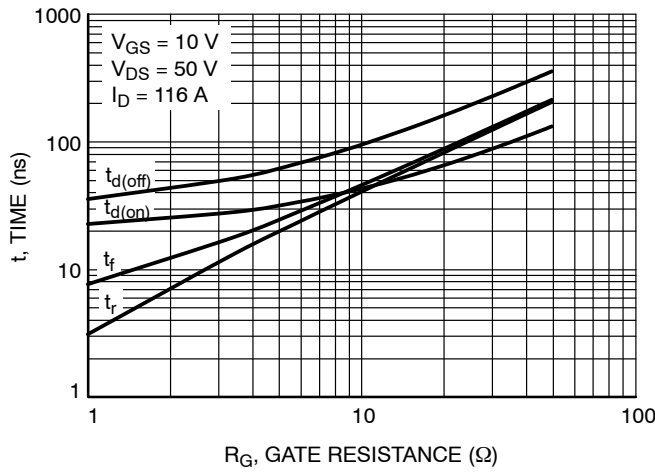


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

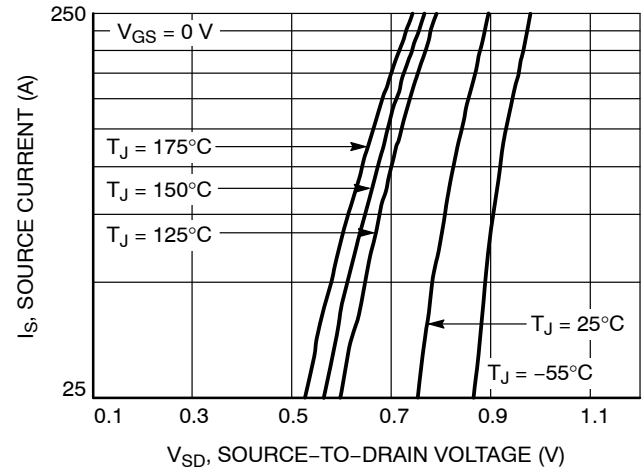


Figure 10. Diode Forward Voltage vs. Current

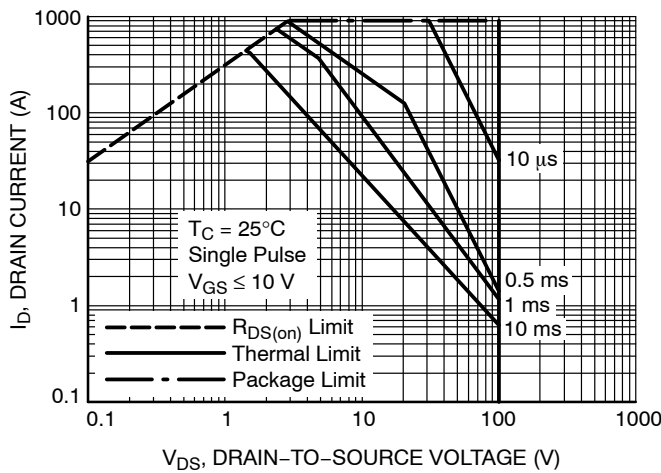


Figure 11. Safe Operating Area

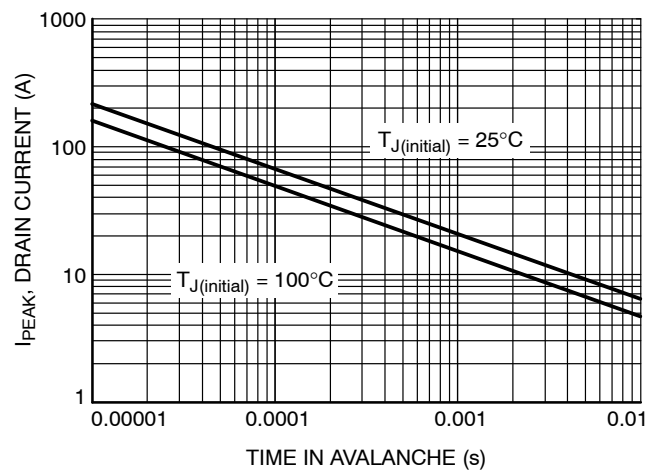


Figure 12. Maximum Drain Current vs. Time in Avalanche

# NTMTSC1D6N10MC

## TYPICAL CHARACTERISTICS

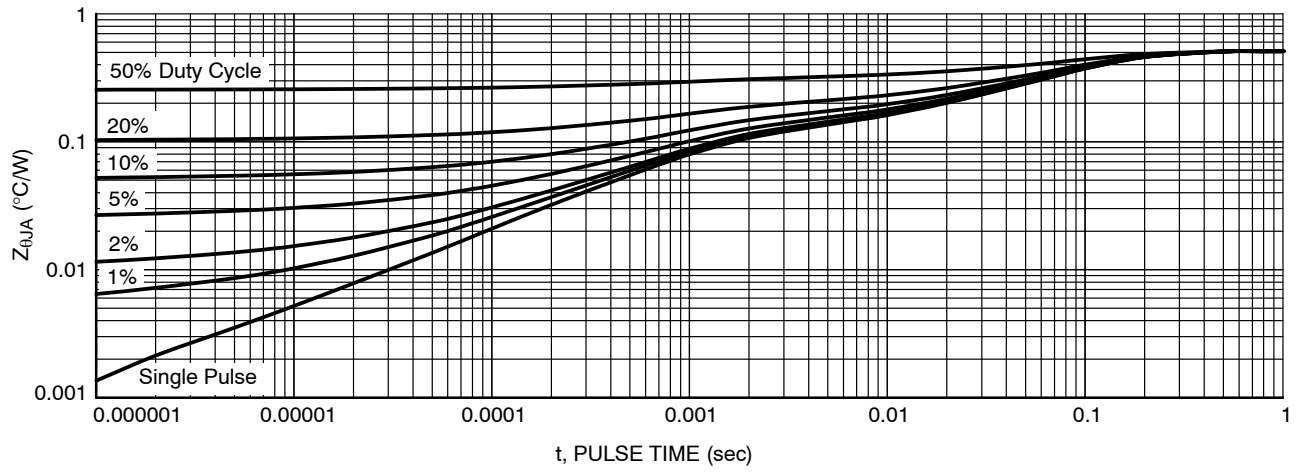


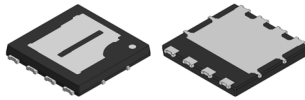
Figure 13. Junction-to-Ambient Transient Thermal Response

### DEVICE ORDERING INFORMATION

| Device            | Marking | Package                         | Shipping <sup>†</sup> |
|-------------------|---------|---------------------------------|-----------------------|
| NTMTSC1D6N10MCTXG | 1D6N10M | POWER 88 Dual Cool<br>(Pb-Free) | 3,000 / Tape & Reel   |

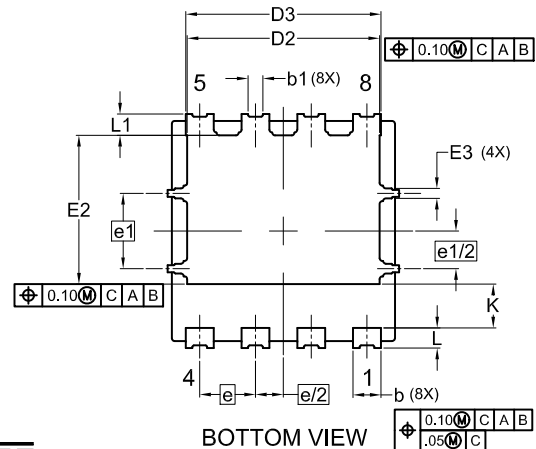
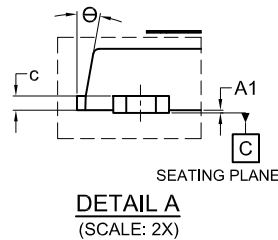
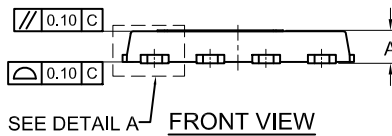
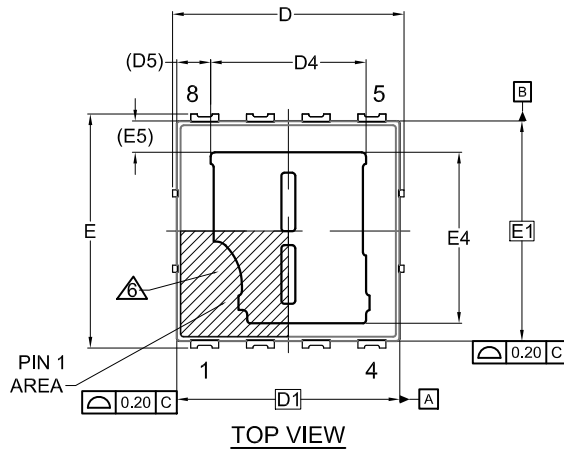
<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

# MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS



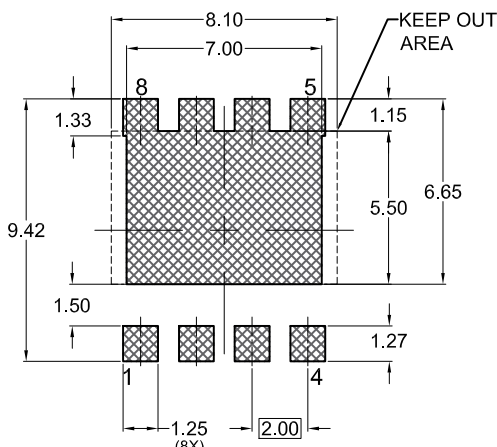
**TDFNW8 8.30x8.40x0.92, 2.00P**  
**CASE 507AS**  
**ISSUE C**

DATE 28 MAY 2024



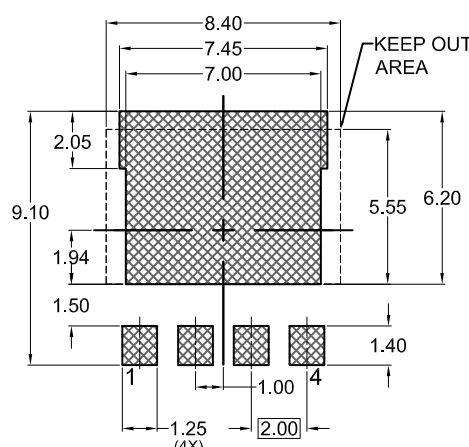
## NOTES:

1. DIMENSIONING & TOLERANCING PER ASME Y14.5M, 2009.
2. CONTROLLING DIMENSION: MILLIMETERS
3. COPLANARITY APPLIES TO THE EXPOSED PADS AS WELL AS THE TERMINALS.
4. DIMENSIONS D1 AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.
5. SEATING PLANE IS DEFINED BY THE TERMINALS. "A1" IS DEFINED AS THE DISTANCE FROM THE SEATING PLANE TO THE LOWEST POINT ON THE PACKAGE BODY.
6. SLOT PARTITION IS OPTIONAL.



## RECOMMENDED LAND PATTERN

\*FOR ADDITIONAL INFORMATION ON OUR PB-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ONSEMI SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.



## UNIVERSAL LAND PATTERN\*

| DIM  | MILLIMETERS |      |      |
|------|-------------|------|------|
|      | MIN.        | NOM. | MAX. |
| A    | 0.82        | 0.92 | 1.02 |
| A1   | 0.00        | —    | 0.05 |
| b    | 0.90        | 1.00 | 1.10 |
| b1   | 0.35        | 0.45 | 0.55 |
| c    | 0.23        | 0.28 | 0.33 |
| D    | 8.20        | 8.30 | 8.40 |
| D1   | 8.00 BSC    |      |      |
| D2   | 6.80        | 6.90 | 7.00 |
| D3   | 6.90        | 7.00 | 7.10 |
| D4   | 5.52        | 5.67 | 5.82 |
| D5   | 1.16 REF    |      |      |
| E    | 8.30        | 8.40 | 8.50 |
| E1   | 7.90 BSC    |      |      |
| E2   | 5.24        | 5.34 | 5.44 |
| E3   | 0.25        | 0.35 | 0.45 |
| E4   | 6.08        | 6.23 | 6.38 |
| E5   | 1.13 REF    |      |      |
| e    | 2.00 BSC    |      |      |
| e/2  | 1.00 BSC    |      |      |
| e1   | 2.70 BSC    |      |      |
| e1/2 | 1.35 BSC    |      |      |
| K    | 1.50        | 1.57 | 1.70 |
| L    | 0.64        | 0.74 | 0.84 |
| L1   | 0.67        | 0.77 | 0.87 |
| Θ    | 0°          | —    | 12°  |

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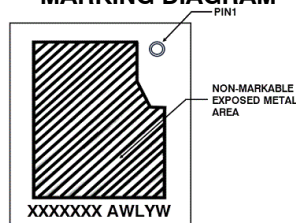
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**CASE 507AS**  
**ISSUE C**

DATE 28 MAY 2024

**GENERIC  
MARKING DIAGRAM\***



XXXX = Specific Device Code  
A = Assembly Location  
WL = Wafer Lot Code  
Y = Year Code  
W = Work Week Code

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

|                         |                                     |                                                                                                                                                                                  |
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